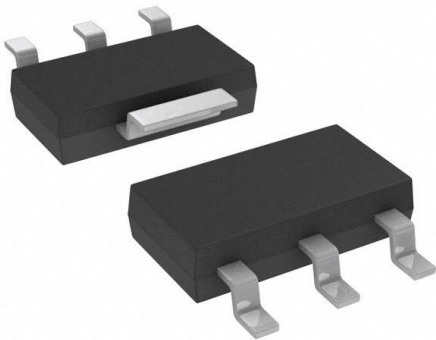


BSP324L6327HTSA1 Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	BSP324L6327HTSA1-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	BSP324L6327HTSA1
Description	MOSFET N-CH 400V 170MA SOT223-4
Detailed Description	N-Channel 400 V 170mA (Ta) 1.8W (Ta) Surface Mount PG-SOT223-4-21



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

BSP324L6327HTSA1

Series:

SIPMOS®

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

400 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

2.3V @ 94µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

PG-SOT223-4-21

Manufacturer:

Infineon Technologies

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

170mA (Ta)

Rds On (Max) @ Id, Vgs:

250hm @ 170mA, 10V

Gate Charge (Qg) (Max) @ Vgs:

5.9 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

154 pF @ 25 V

Power Dissipation (Max):

1.8W (Ta)

Mounting Type:

Surface Mount

Package / Case:

TO-261-4, TO-261AA

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095



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SIPMOS® Power-Transistor Feature

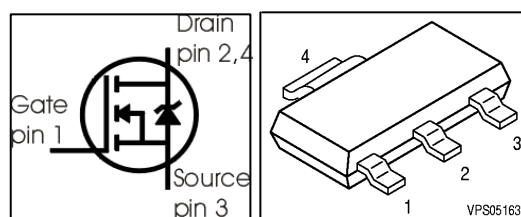
- N-Channel
- Enhancement mode
- Logic Level
- dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101



Product Summary

V_{DS}	400	V
$R_{DS(on)}$	25	Ω
I_D	0.17	A

SOT-223



Type	Package	Pb-free	Packaging	Tape and Reel Information	Marking
BSP324	PG-SOT223	Yes	Non dry	L6327: 1000 pcs/reel	BSP324

Maximum Ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_A=25\text{ }^\circ\text{C}$ $T_A=70\text{ }^\circ\text{C}$	I_D	0.17 0.14	A
Pulsed drain current $T_A=25\text{ }^\circ\text{C}$	$I_{D\text{ puls}}$	0.68	
Reverse diode dv/dt $I_S=0.17\text{A}$, $V_{DS}=320\text{V}$, $di/dt=200\text{A}/\mu\text{s}$, $T_{j\text{max}}=175\text{ }^\circ\text{C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
ESD Class (JESD22-A114-HBM)		1A (>250V, <500V)	
Power dissipation $T_A=25\text{ }^\circ\text{C}$	P_{tot}	1.8	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/150/56	



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Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point (Pin 4)	R_{thJS}	-	16	25	K/W
SMD version, device on PCB:	R_{thJA}	-	85	115	
@ min. footprint		-	45	70	
@ 6 cm ² cooling area ¹⁾		-			

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0, I_D=250\mu\text{A}$	$V_{(BR)DSS}$	400	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=94\mu\text{A}$	$V_{GS(th)}$	1.3	1.9	2.3	
Zero gate voltage drain current $V_{DS}=400\text{V}, V_{GS}=0, T_j=25^\circ\text{C}$ $V_{DS}=400\text{V}, V_{GS}=0, T_j=125^\circ\text{C}$	I_{DSS}	-	0.01	0.1	μA
		-	-	10	
Gate-source leakage current $V_{GS}=20\text{V}, V_{DS}=0$	I_{GSS}	-	10	100	nA
Drain-source on-state resistance $V_{GS}=4.5\text{V}, I_D=0.05\text{A}$	$R_{DS(on)}$	-	14.3	22	Ω
Drain-source on-state resistance $V_{GS}=10\text{V}, I_D=0.17\text{A}$	$R_{DS(on)}$	-	13.6	25	

¹⁾ Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (single layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.



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Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 0.14\text{A}$	0.09	0.19	-	S
Input capacitance	C_{iss}	$V_{GS} = 0$, $V_{DS} = 25\text{V}$,	-	103	154	pF
Output capacitance	C_{oss}	$f = 1\text{MHz}$	-	9.2	13.6	
Reverse transfer capacitance	C_{rss}		-	3.8	5.7	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 225\text{V}$, $V_{GS} = 10\text{V}$,	-	4.6	6.9	ns
Rise time	t_r	$I_D = 0.17\text{A}$, $R_G = 6\Omega$	-	4.4	6.6	
Turn-off delay time	$t_{d(off)}$		-	17	25	
Fall time	t_f		-	68	102	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 320\text{V}$, $I_D = 0.17\text{A}$	-	0.35	0.45	nC
Gate to drain charge	Q_{gd}		-	2.17	2.82	
Gate charge total	Q_g	$V_{DD} = 320\text{V}$, $I_D = 0.17\text{A}$, $V_{GS} = 0$ to 10V	-	4.54	5.9	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 320\text{V}$, $I_D = 0.17\text{A}$	-	3.6	-	V

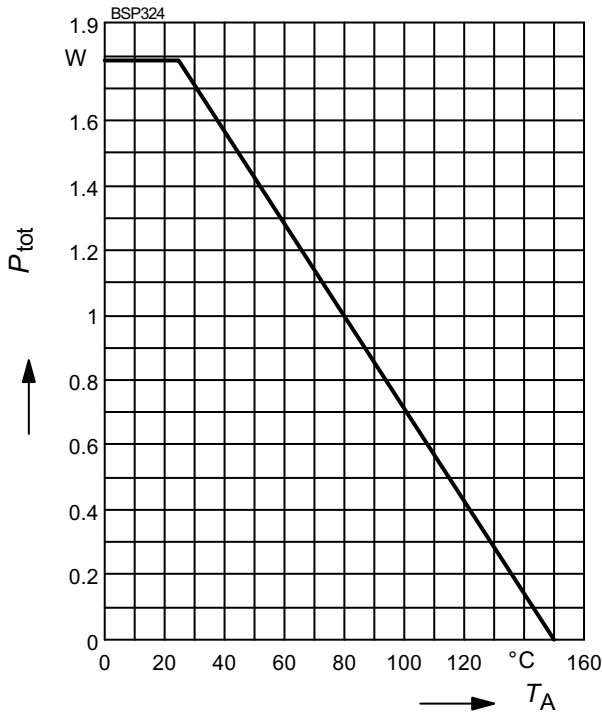
Reverse Diode

Inverse diode continuous forward current	I_S	$T_A = 25\text{ }^\circ\text{C}$	-	-	0.17	A
Inv. diode direct current, pulsed	I_{SM}		-	-	0.68	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0$, $I_F = 0.17\text{A}$	-	0.8	1.2	V
Reverse recovery time	t_{rr}	$V_R = 200\text{V}$, $I_F = I_S$,	-	85	127	ns
Reverse recovery charge	Q_{rr}	$di_F/dt = 100\text{A}/\mu\text{s}$	-	104	156	



1 Power dissipation

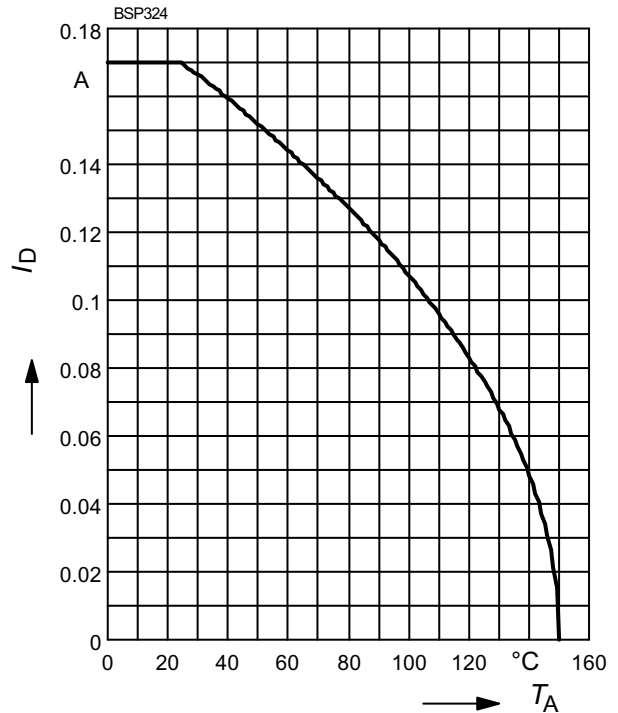
$P_{tot} = f(T_A)$



2 Drain current

$I_D = f(T_A)$

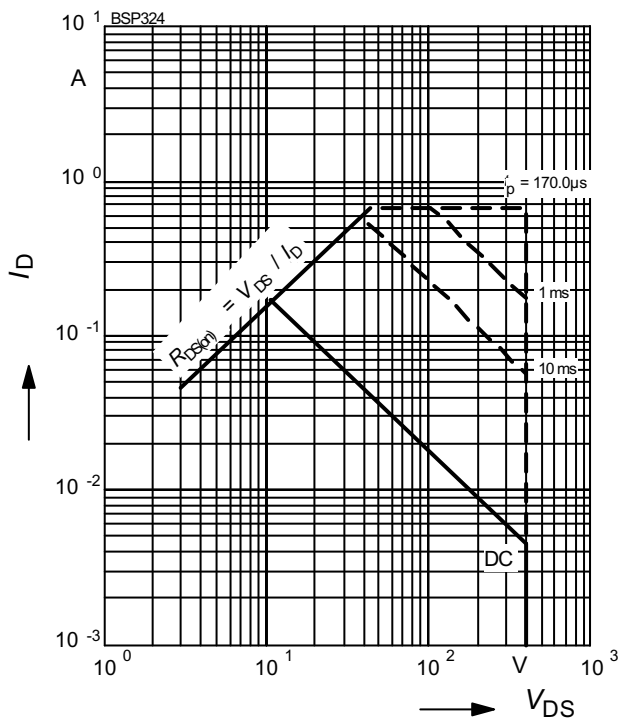
parameter: $V_{GS} \geq 10\text{ V}$



3 Safe operating area

$I_D = f(V_{DS})$

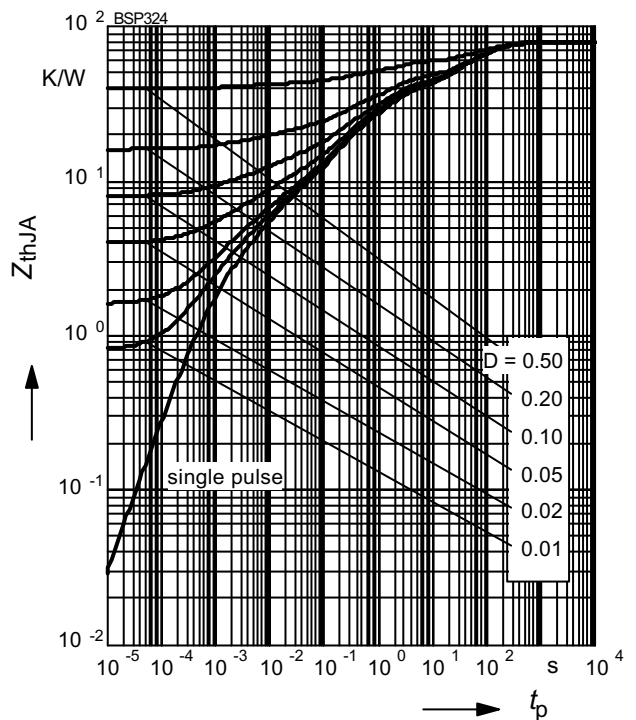
parameter: $D = 0, T_A = 25\text{ °C}$



4 Transient thermal impedance

$Z_{thJA} = f(t_p)$

parameter: $D = t_p/T$

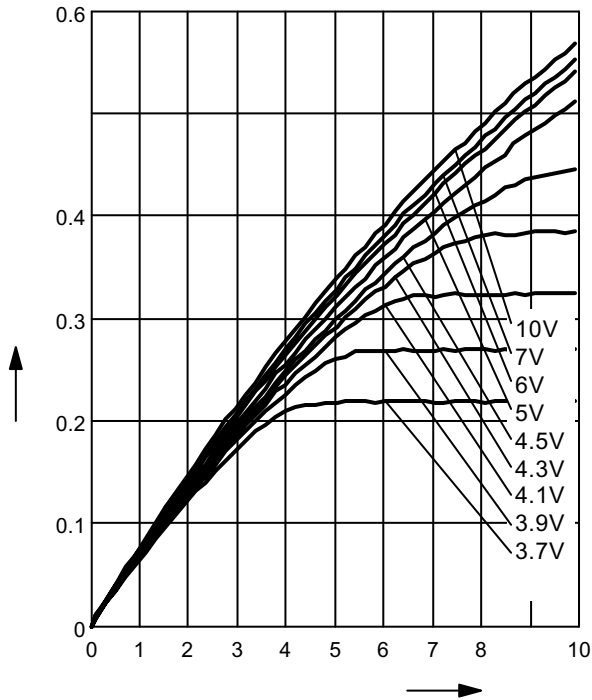




5 Typ. output characteristic

$I_D = f(V_{DS})$

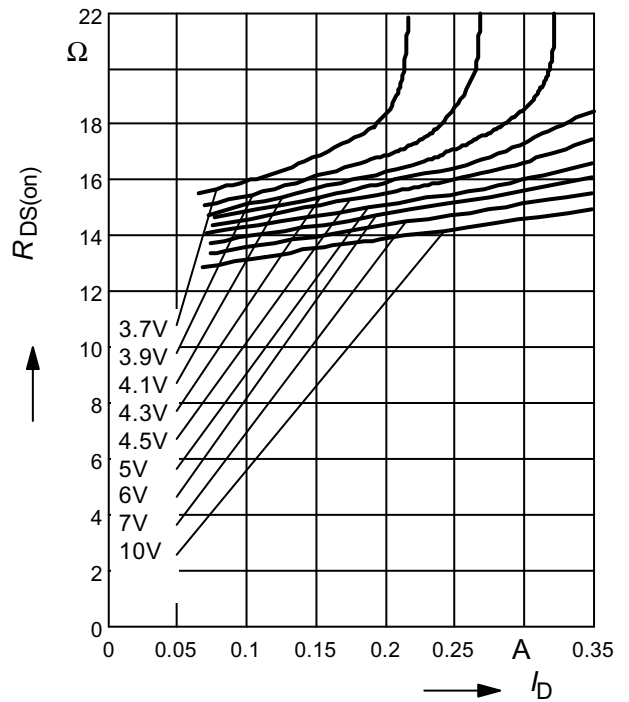
parameter: $T_j = 25\text{ }^\circ\text{C}$, V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

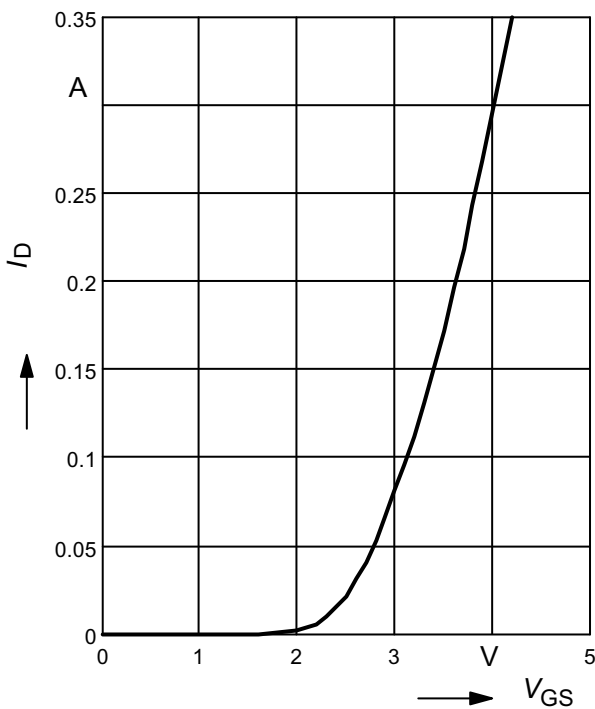
parameter: $T_j = 25\text{ }^\circ\text{C}$, V_{GS}



7 Typ. transfer characteristics

$I_D = f(V_{GS})$; $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

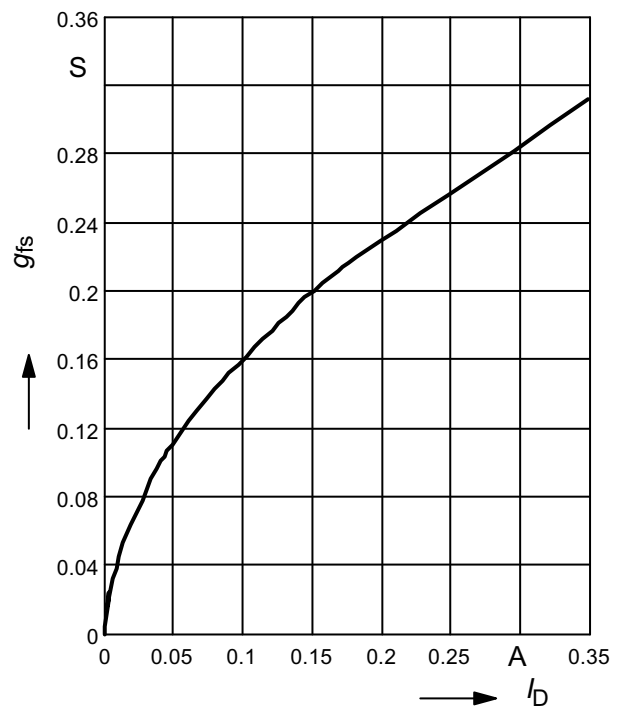
parameter: $T_j = 25\text{ }^\circ\text{C}$



8 Typ. forward transconductance

$g_{fs} = f(I_D)$

parameter: $T_j = 25\text{ }^\circ\text{C}$

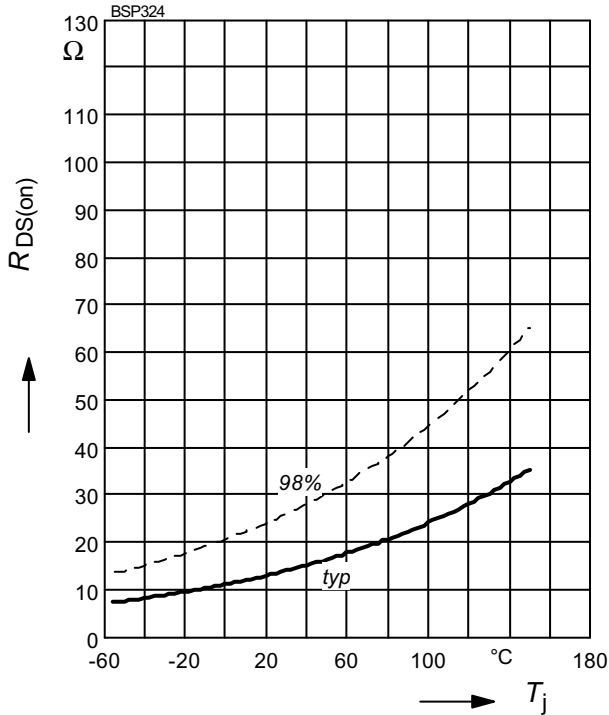




9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

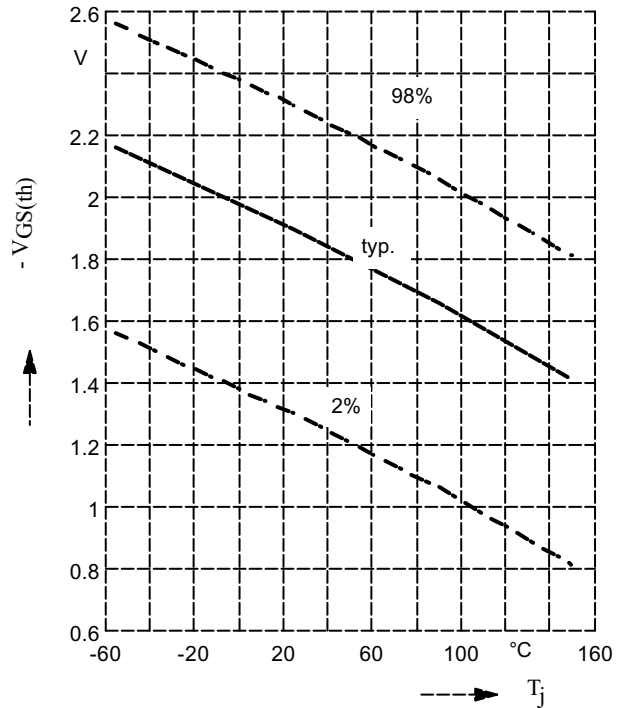
parameter : $I_D = 0.17 \text{ A}$, $V_{GS} = 10 \text{ V}$



10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j)$

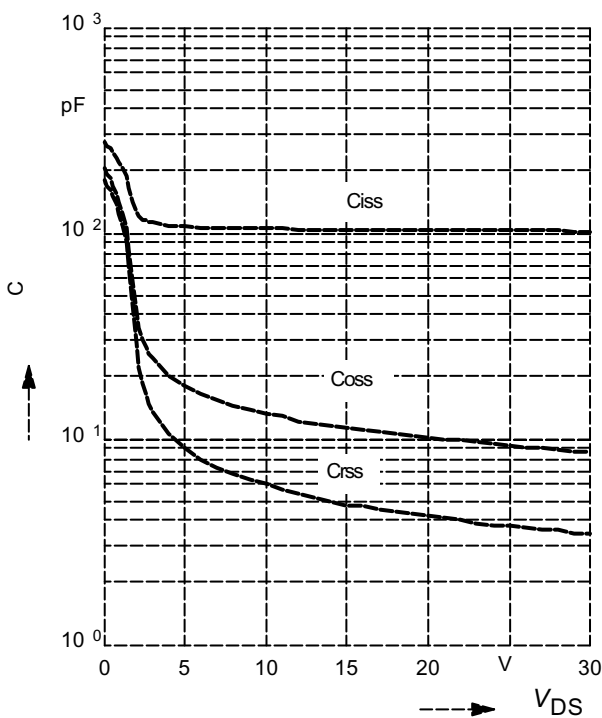
parameter: $V_{GS} = V_{DS}$; $I_D = 94 \mu\text{A}$



11 Typ. capacitances

$C = f(V_{DS})$

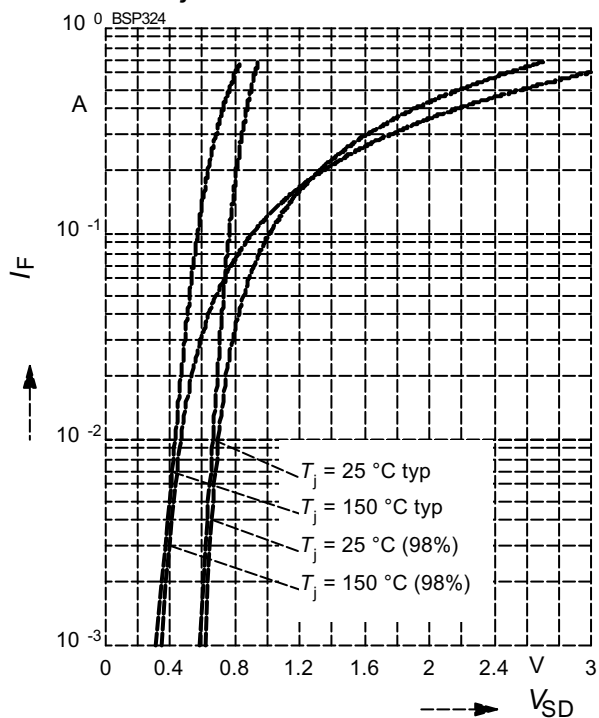
parameter: $V_{GS}=0$, $f=1 \text{ MHz}$, $T_j = 25 \text{ }^\circ\text{C}$



12 Forward character. of reverse diode

$I_F = f(V_{SD})$

parameter: T_j



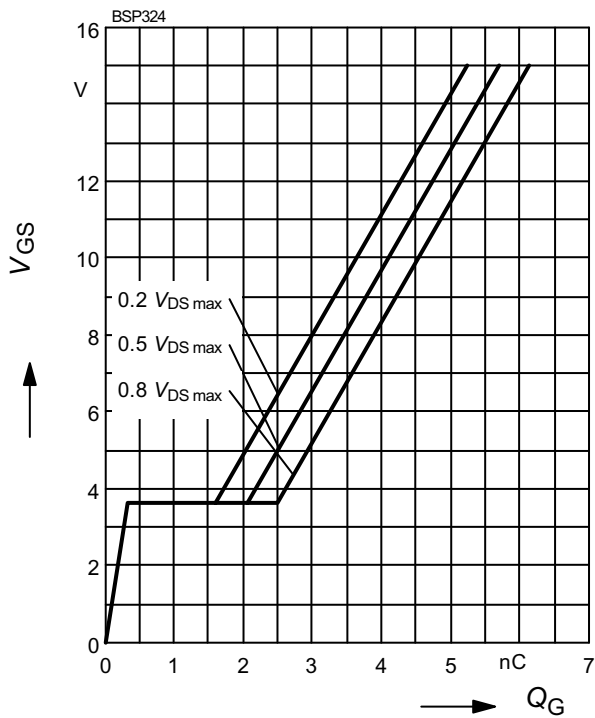


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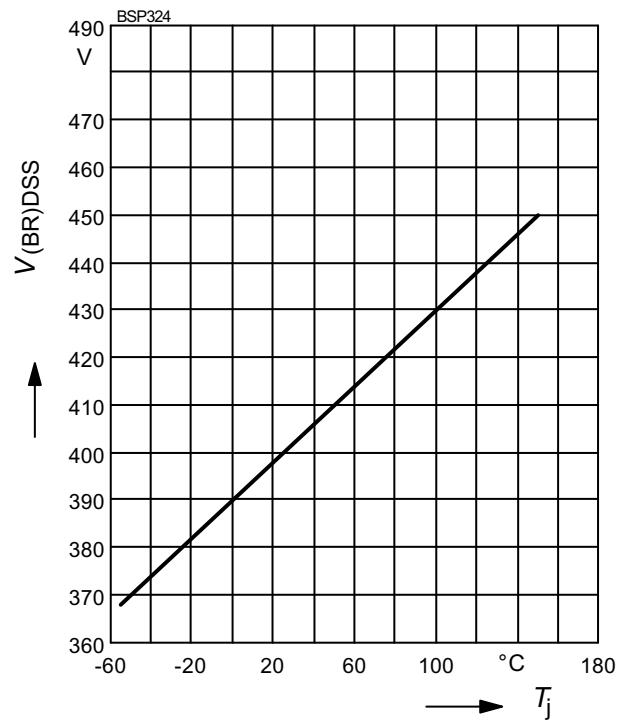
BSP324

13 Typ. gate charge

 $V_{GS} = f(Q_G)$; parameter: V_{DS} ,

 $I_D = 0.17 \text{ A pulsed}, T_j = 25 \text{ }^\circ\text{C}$


14 Drain-source breakdown voltage

 $V_{(BR)DSS} = f(T_j)$




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